

RFFEM07-10 Front End Module operates from 5 – 7 GHz and can be used in low power C band application. The input and output are matched to 50 ohms with on-chip DC blocking capacitors. The device is specifically designed to use in point-to-point radios for 5G RF Transceiver & SATCOM. The technology used to design front-end module is 0.1um GaAs pHEMT process. Results are shown in datasheet with all parasitics & coupling effects at desired frequency.

Features:

- RF Frequency: 5-7 GHz
- TX Gain of 27 dB
- RX Gain of 12 dB
- TX Output P1dB of 17.8 dBm
- Noise Figure of 3 dB
- TX Bias: VDD=4V, VGG= - 0.6V, ID= 156mA
- RX Bias: VDD=4V, VGG= - 0.6V, ID= 15.8mA
- Die size: 2.4 mm x 2.4 mm

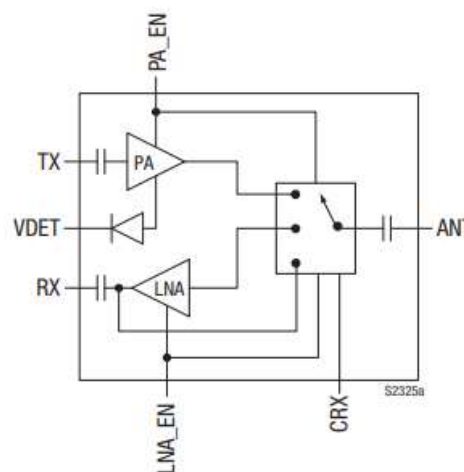
Application:

- Wi-Fi 6
- Bluetooth Application
- Zigbee
- Satellite Communication
- TDD/FDD System
- Internet of Things

Tech Specs:

- Part Number: RFFEM07-10
- Provider: RFIC Solutions Inc.
- Foundry node: 0.1um GaAs pHEMT Win Semiconductors
- Porting: IP can be ported to 65nm Si / CMOS node

Functional Block Diagram:



Deliverables:

- Schematic and Netlist
- Abstract Model (.lib file)
- Layout View(Optional)
- Behavioral model (Circuit & EM simulation)
- Extracted View(Optional)
- GDSII
- DRC, LVS, Antenna report
- Test bench with configuration(Optional)
- Documentation

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